## **Photodetectors**

Туре	Construction Spectr		Peak	Max. Power Diss. (mW)	Diode Rev. Volts (V)	Transistor Max. Ratings			Typical Light Current		Typical Dark Curren <b>t</b>		Case	Lead	Man
Ahe			Response			V <sub>C80</sub>	V <sub>CEO</sub>	V <sub>EBO</sub> (V)	Aπ	at V <sub>CE</sub>	пА	at V <sub>CE</sub>	Outline	Info.	mane
										_					
LS616	Si	**	-	50	-	-	-	-	5mA	5	25	30	-	127	ΤI
LS617	Si		-	50	-	-	-	-	6mA	5	25	30	-	127	ΤI
LS618	Si Si	9	-	50	-	-	-	-	7mA	5	25	30	-	127	ΤΙ
LS6 19 MAL 100	51 Si	0	-	50 200	-	- 50	- 30	-	8mA 200	5 5	25 100	30 5	-	127 05	TI u
															-
MEL31	Si	n	-	200	-	40	30	-	10	5	50	5	TO-106	05	u
MEL32	Si		-	200	-	60	40	-	30	5	50	5	TO-106	05	u
MEL 100	Si		-	200	-	50	30	-	200	5	100	5	TO-106	05	u
MEPT 100A	5i 5i		-	200 200	-	50 50	30	-	200 1-0	5	100	5 5	TO-106	05	u 
ALF FIBUR	31		-	مان	-	50	30	-	1rA	5	100	כ	TO-106	05	u
MEPT 1008	Si	н	-	200	-	50	30	-	1.3mA		100	5	T0-106	133	ш
MRD 160	5 <u>f</u>	n 11	800	-	-	40	48	-	1.5mA		100	20	-	-	Ma
MRD300	Si	11	800	-	-	50	50	-	7.5mA		25	20	-	-	Mo
MRD310	Si	11	800	-	-	50	50	-	2.5mA		25	20	-	-	Mo
MRD450	Si	.,	800	-	-	40	40	-	4mA	-	100	20	-	-	Mo
MRD500	Si	u .	800	-	100	-	-	-	9	-	2	20	-	-	· Mo
MRD510	51	a .	800	-	100	-	-	-	2	-	2	20	-	-	Mo
MRD601	Si	н	800	-	-	50	50	-	1.5mA		25	30	-	-	Mo
MRD602	51	a a	800	-	-	50	50	-	3.5mA	٠ -	25	30	-	-	Ma
MRD603	5 <b>i</b>	11	800	-	-	50	50	-	6mA	-	25	30	-	-	MO
MRD604	Si	11	800	_	_	50	50	-	8.5mA	٠ -	25	30	_	-	Mo
MRD3050	Si	**	800	-	-	30	30	-	200	-	100	20	-	_	Mo
MRD3051	Si	Ħ	800	-	-	30	30	-	200	-	100	20	_	-	Mo
MRD3054	Si	n	800	-	-	30	30	-	1.8mA	٠ -	100	20	_	-	Mo
MRD3055	Si	Ħ	800	-	-	30	30	-	2.5mA	-	100	20	-	-	Ma
MRD3056	Si	n	800	_	_	30	30	_	1.2mA	٠ -	100	20	-	_	Mo
TIL63	Si	Ħ	-	50	_	_	-	_	400	5	25	30	_	-	TI
TIL64	Si	11	-	50	_	-	_	-	400	5	25	30	-	_	TI
TIL65	51	н	_	50	-	-	_	_	1mA	5	25	30	_	_	TI
TIL66	Si	H	-	50	-	-	-	-	2.5mA	5	25	30	-	-	TI
TIL67	Si	et	_	50	_	_	_	_	6mA	5	25	30	_	_	TI
TIL78	Si	H.	_	50	_	_	_	_	1mA	5	25	30	_	_	TI
TIL81	51	R	_	250	_	_	_	_	5mA	5	100	10	_	-	ΤÎ
TIL99	Si	n	_	250	_	_	_	_	1mA	5	100	10	_	_	ΤÎ
TIL401	Si	n	-	50	-	-	-	-	500	50	25	30	-	-	TI
TIL402	Si	"	_	50	_	_	_	_	2mA	5	25	30	_	_	ΤI
T1L403	S1	U	_	50	_	_	_	-	5mA	5	25	30	-	-	71
TIL404	Si	II .	-	50	-	_	-	-	8mA	5	25	30	-	-	TI
TIL4D5	Si		_	50	_	-	_	-	10mA	5	25	30	-	_	ΤÎ
ZM100	Si NPN	и	780	300	-	35	35	10	-	-	1uA	10	TO-18	05	Fe
ZM110	Si NPN Tra			300	-	35	35	5	-	-	25	10	TO-18	05	Fe
2N5777	Si NPN	"	800	200	-	25	25	8	500	5	100	12	-	09	GE
2N5778	Si NPN		800	200	-	40	40	12	500	5	100	12	-	D <del>9</del>	GE
2N5779	Si NPN		800	200	-	25	25	8	2mA	5	100	12	-	09	GÉ
2N5780	Si NPN	1)	800	200	-	40	40	12	2mA	5	100	12	-	09	GE

## Características:

VcE(max)	50 V
Ptot	50 mW
Corrente no escuro (max	)100 nA
Corrente no claro (tip)	1 μΑ
VCE(SAT)	

